

**What is claimed is:**

1. A semiconductor light emitting element of a monolithic structure, comprising:
  - a first-conductivity-type semiconductor substrate;
  - 5 an active layer formed on the first-conductivity-type semiconductor substrate;
  - a second-conductivity-type clad layer formed on the active layer; and
  - 10 a current diffusion layer formed on the second-conductivity-type clad layer,
    - wherein the active layer is of a first conductivity type.
2. The element of claim 1, wherein the semiconductor substrate is a GaAs substrate, and the active layer is a semiconductor layer containing Al, Ga, As, In and/or P as  
15 constituent atoms.
3. The element of claim 1, wherein the active layer contains Si or Se atoms as first-conductivity-type impurities.
4. The element of claim 1, wherein the active layer contains Zn or Mg as first-conductivity-type impurities.
- 20 5. The element of claim 1, wherein the active layer contains first-conductivity-type impurities in a concentration between  $3 \times 10^{16}$  and  $10 \times 10^{16}$  cm<sup>-3</sup>.
6. The element of claim 1, wherein a spacer layer is provided between the active layer and the  
25 second-conductivity-type clad layer.

7. The element of claim 6, wherein the spacer layer is either a non-doped layer or a second-conductivity-type layer.
8. The element of claim 6, wherein the spacer layer has a thickness of 0.1 to 0.2  $\mu$  m.

5 9. The element of claim 6, wherein the spacer layer is formed of the same constituent atoms in the same composition as is the case of the second-conductivity-type clad layer.

10. The element of claim 1 or 9, wherein the active layer is formed of GaAlInP, the second-conductivity-type clad layer is

10 also formed of GaAlInP, and the Al mixed crystal ratio of the active layer is lower than that of the second-conductivity-type clad layer.

11. The element of claim 10, wherein the Al mixed crystal ratios of the second-conductivity-type clad layer and the

15 spacer layer are approximately 0.7, and that of the active layer is approximately 0.3.